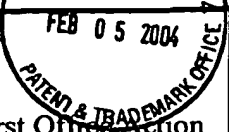
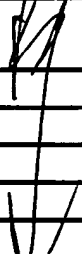
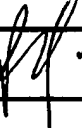


FORM PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Atty. Docket No. <b>86655SHS</b> Customer No. 01333	Serial No. <b>10/722,309</b>
If AFTER the later date of the first Office Action or 3 months from filing, use only with Rule 97(E) Certificate or Fee		Applicant: <b>Liya Regel, et al</b>	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		Filing Date <b>25 November 2003</b>	Group

U.S. PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	US 2003/0173895 A1	09-18-2003	Yoshifumi Kato et al.	313	504	01-30-2003
	5,920,080	07-06-1999	Gary W. Jones	257	40	05-08-1998
	6,198,218	03-06-2001	Koji Kobashi et al.	313	504	12-18-1998
	6,525,335	02-25-2003	Michael R. Krames et al.	257	13	11-06-2000
	6,560,398	05-06-2003	William R. Roach et al.	385	147	10-19-2000
	6,608,449	08-19-2003	Takeshi Fukunaga	313	169.3	05-08-2001

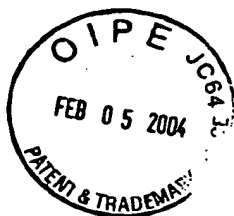
FOREIGN PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES   NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
	A. Gicquel, K. Hassouni, F. Silva and J. Achard, "CVD diamond films: from growth to applications," <i>Current Applied Physics</i> 1 (2001), pp. 479-496.
	"Diamond Films" Recent Developments," Volume 23, No. 9 of the MRS Bulletin (September 1998), Materials Research Society, Warrendale, Pennsylvania.
	L.L. Regel and W.R. Wilcox, "Diamond film deposition by chemical vapor transport," <i>Acta Astronautica</i> 48 (2001), pp. 129-144.
9	W.L. Wang, K.J. Liao, R.Q. Zhang and C.Y. Kong, "Investigation of organic light emitting devices using boron-doped diamond electrodes," <i>Materials Science and Engineering B85</i> (2001), pp. 169-171.
•	M.J. Ulczynski, B. Wright and D.K. Reinhard, "Diamond-coated glass substrates," <i>Diamond and Related Materials</i> 7 (1998), pp. 1639-1646.
•	J. Stiegler, A. Bergmaier, J. Michler, Y. von Kaenel, G. Dollinger, E. Blank, "Impurity and defect incorporation in diamond films deposited at low substrate temperatures," <i>Diamond and Related Materials</i> 7 (1998), pp. 193-199.
•	C. Jinsheng, W. Xuejun, Z. Zhihao and Y. Fengyuan, "Nucleation and growth of diamond on silicon substrate coated with polymer," <i>Thin Solid Films</i> 346 (1999), pp. 120-124.
•	Z. Sun, X. Shi, X. Wang, B.K. Tay, H. Yang and Y. Sun, "Morphological features of diamond films depending on substrate temperatures via a low pressure polymer precursor process in a hot filament reactor," <i>Diamond and Related Materials</i> 7 (1998), pp. 939-943.
•	V.J. Trava-Airoldi, B.N. Nobrega, E.J. Corat, E. del Bosco, N.F. Leiter and V. Baranauskas, "Low temperature chemical vapour deposition of diamond on tungsten carbides using CF <sub>4</sub> gas doping for machine tool applications," <i>Vacuum</i> 46 (1995) 5-8.
•	L. Dong, B. Ma and G. Dong, "Diamond deposition at low temperature by using CH <sub>4</sub> /H <sub>2</sub> gas mixture," <i>Diamond and Related Materials</i> 11 (2002), pp. 1697-1702.
•	J. Petherbridge, P.W. May, S.R.J. Pearce, K.N. Rosser and M.N. Ashfold, "Molecular beam mass spectrometry investigations of low temperature diamond growth using CO <sub>2</sub> /CH <sub>4</sub> plasmas," <i>Diamond and Related Materials</i> 10 (2001), pp. 393-398.
•	I. Schmidt and C. Benndorf, "Low temperature CVD materials: AlZn and glass," <i>Diamond and Related Materials</i> 10 (2001), pp. 347-351.

9/24/05

	A. Li Tolt, L. Heatherly, R.E. Clausing, R.W. Shaw and C.S. Feigerle, "HFCD of diamond at low substrate and low filament temperatures," pp. 303-311 in <u>Electrochemical Society Proceedings Volume 95-4, Proceedings of the Fourth International Symposium on Diamond Materials</u> , edited by K.V. Ravi and J.P. Dismukes, The Electrochemical Society, Pennington, NJ (1995).
	A. Hatta and A. Hiraki, "Low temperature chemical vapor deposition," pp. 887-899, in <u>Handbook of Industrial Diamonds and Diamond Films</u> , edited by M.A. Prelas, G. Popovici and L.K. Bigelow, Marcel Dekker, NY (1998).
	J.G. Buijnster, P. Shankar, W.J.P. van Enckevort, J.J. Schermer and J.J. ter Meulen, "The effect of nitriding on the diamond film characteristics on chromium substrates," <u>Diamond and Related Materials</u> 11 (2002), pp. 1760-1768.
	B.V. Spitsyn, "The state of the art in studies of diamond synthesis from the gaseous phase and some unsolved problems," in <u>Applications of Diamond Films and Related Materials</u> , edited by Y. Tzeng, M. Yoshikawa, M. Murakami and A. Feldman. Elsevier, Amsterdam (1991). <i>no page number</i>
	B.V. Spitsyn, "Crystallization of diamond by the chemical transport reaction: thermodynamics and kinetics," pp. 61-72, in <u>Electrochemical Society Proceedings Volume 95-4, Proceedings of the Fourth International Symposium on Diamond Materials</u> , edited by K.V. Ravi and J.P. Dismukes, The Electrochemical Society, Pennington, NJ (1995).
	L.L. Regel, T. Takagi and W.R. Wilcox, "Centrifugal diamond film processing," pp. 221-227, in <u>Centrifugal Materials Processing</u> , edited by L.L. Regel and W.R. Wilcox, Plenum Press, NY (1997).
	H.K. Woo, C.S. Lee, I. Bello. St. T. Lee, K.W. Wong and N.B. Wong, "Oriented diamond growth on silicon (111) using a solid carbon source," <u>J. Applied Physics</u> 83 (1998), pp. 4187-4192.
	S.D. Shin, N.M. Hwang and D.Y. Kim, "High rate of diamond deposition through graphite etching in a hot filament CVD reactor," <u>Diamond and Related Materials</u> 11 (2002), pp. 1337-1343.
	L.L. Regel and W.R. Wilcox, "Selective patterned deposition of diamond using a new technique," <u>J. Mat. Sci. Lettr.</u> 18 (1999), pp. 427-430.
	Y. Takagi, L.L. Regel and W.R. Wilcox, "New method for diamond film deposition under different gravity conditions," <u>Trans. Mat. Res. Soc. Japan</u> 24 (1999), pp. 513-518.
	L.L. Regel and W.R. Wilcox, "Deposition of diamond on graphite and carbon felt from graphite heated in hydrogen at low pressure," <u>J. Mat. Sci. Lettr.</u> 19 (2000), pp. 455-457.

EXAMINER	DATE CONSIDERED <u>9/24/05</u>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



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		Applicant: <b>Liya Regel, et al</b>			
		Filing Date <b>25 November 2003</b>		Group <b>1762</b>	

U.S. PATENT DOCUMENTS						
Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>PK</i>	5,863,324	01-26-1999	Koji Kobashi et al.	117	89	07-11-1996
<i>PK</i>	US 2003/0108672 A1	06-12-2003	Yoshiki Takagi	427	249.8	10-10-2002
	JP 08 225394 A	09-03-1996	Yamagishi Kenichiro	C30 B	29/04	10-30-1995

FOREIGN PATENT DOCUMENTS						
Examiner Initial	DOCUMENT NUMBER	DATE	COUNTRY NAME	CLASS	SUBCLASS	TRANSLATION YES   NO
<i>PK</i>	JP 08 225394 A	09-03-1996	Kenichiro et al			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)
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